# 4-Bit Dual-Supply **Non-Inverting Level Translator**

The NLSV4T244E is a 4-bit configurable dual-supply voltage level translator. The input A<sub>n</sub> and output B<sub>n</sub> ports are designed to track two different power supply rails, V<sub>CCA</sub> and V<sub>CCB</sub> respectively. Both supply rails are configurable from 0.9 V to 4.5 V allowing universal low-voltage translation from the input  $A_n$  to the output  $B_n$  port.

#### **Features**

- Wide V<sub>CCA</sub> and V<sub>CCB</sub> Operating Range: 0.9 V to 4.5 V
- High-Speed w/ Balanced Propagation Delay
- Inputs and Outputs have OVT Protection to 4.5 V
- Non-preferential V<sub>CCA</sub> and V<sub>CCB</sub> Sequencing
- Outputs at 3-State until Active V<sub>CC</sub> is Reached
- Power-Off Protection
- Outputs Switch to 3-State with V<sub>CCB</sub> at GND
- Data Rate > 200 Mbps @  $V_{CCA} = 1.8 \text{ V}$ ,  $V_{CCB} = 3.3 \text{ V}$ ,  $R_L = 2 \text{ k}$ .ypical Applications

  • Mobile Phones, PDAs, Other Portable Devices

  Important Information

  • ESD Protection for All Processing Proc

HBM (Human Body Model) > 2000 V MM (Machine Model) > 400 V THIS DE



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#### **MARKING DIAGRAMS**



UQFN12 **MU SUFFIX** CASE 523AE



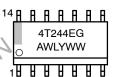
 Specific Device Code = Date Code

= Pb-Free Package

(Note: Microdot may be in either location)



SOIC-14 D SUFFIX





TSSOP-14 **DT SUFFIX CASE 948G** 



Assembly Location

I WI Wafer Lot Y, YY Year W. WW Work Week = Pb-Free Package

(Note: Microdot may be in either location)

## **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>
NLSV4T244EMUTAG	UQFN12 (Pb-Free)	3000/Tape & Reel
NLSV4T244EDR2G	SO-14 (Pb-Free)	2500/Tape & Reel
NLSV4T244EDTR2G	TSSOP14 (Pb-Free)	2500/Tape & Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

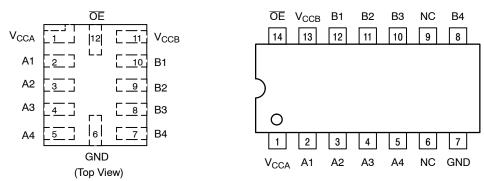


Figure 1. Pin Assignments

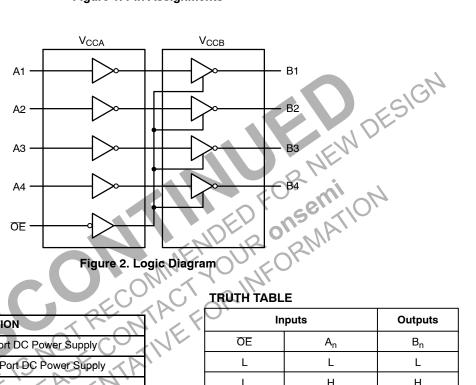


Figure 2. Logic Diagram

#### **PIN ASSIGNMENT**

PIN	FUNCTION
V <sub>CCA</sub>	Input Port DC Power Supply
V <sub>CCB</sub>	Output Port DC Power Supply
GND	Ground
A <sub>n</sub>	Input Port
B <sub>n</sub>	Output Port
OE 1/13	Output Enable

) In	Outputs	
ŌĒ	A <sub>n</sub>	B <sub>n</sub>
L	L	L
L	Н	Н
Н	Х	3-State

#### **MAXIMUM RATINGS**

Symbol	Rating	Condition	Value	Unit	
V <sub>CCA</sub> , V <sub>CCB</sub>	DC Supply Voltage			-0.5 to +5.5	V
VI	DC Input Voltage	A <sub>n</sub>		-0.5 to +5.5	V
V <sub>C</sub>	Control Input	OE		-0.5 to +5.5	V
Vo	DC Output Voltage (Power Down)	B <sub>n</sub>	$V_{CCA} = V_{CCB} = 0$	-0.5 to +5.5	V
	(Active Mode)	B <sub>n</sub>		-0.5 to +5.5	V
	(Tri-State Mode)	B <sub>n</sub>		-0.5 to +5.5	V
I <sub>IK</sub>	DC Input Diode Current		V <sub>I</sub> < GND	-20	mA
I <sub>OK</sub>	DC Output Diode Current		V <sub>O</sub> < GND	-50	mA
Io	DC Output Source/Sink Current			±50	mA
I <sub>CCA</sub> , I <sub>CCB</sub>	DC Supply Current Per Supply Pin			±100	mA
I <sub>GND</sub>	DC Ground Current per Ground Pin			±100	mA
T <sub>STG</sub>	Storage Temperature Range			-65 to +150	°C
TJ	Junction Temperature			+125	°C
$\theta_{\sf JA}$	Junction-to-Ambient Thermal Resistance			53	°C/W
$\Psi_{JC(top)}$	Junction-to-Case (Top) Thermal Resistance			10	°C/W

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

### **RECOMMENDED OPERATING CONDITIONS**

Symbol	Parameter	Min	Max	Unit
V <sub>CCA</sub> , V <sub>CCB</sub>	Positive DC Supply Voltage	0.9	4.5	V
VI	Bus Input Voltage	GND	4.5	V
V <sub>C</sub>	Control Input OE	GND	4.5	V
V <sub>IO</sub>	Bus Output Voltage (Power Down Mode) B <sub>n</sub>	GND	4.5	V
	(Active Mode) B <sub>n</sub>	GND	V <sub>CCB</sub>	٧
	(Tri-State Mode) B <sub>n</sub>	GND	4.5	V
T <sub>A</sub>	Operating Temperature Range	-40	+85	°C
Δt / ΔV	Input Transition Rise or Rate $V_{lr}$ , from 30% to 70% of $V_{CG}$ ; $V_{CC}$ = 3.3 V ±0.3 V	0	10	nS

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

### DC ELECTRICAL CHARACTERISTICS

					−40°C to	o +85°C	
Symbol	Parameter	Test Conditions	V <sub>CCA</sub> (V)	V <sub>CCB</sub> (V)	Min	Max	Uni
V <sub>IH</sub>	Input HIGH Voltage		3.6 – 4.5	0.9 – 4.5	2.2	-	V
	(An, $\overline{OE}$ )		2.7 – 3.6		2.0	_	
			2.3 – 2.7		1.6	-	
			1.4 – 2.3		0.65 * V <sub>CCA</sub>	_	
			0.9 – 1.4		0.9 * V <sub>CCA</sub>	_	
$V_{IL}$	Input LOW Voltage		3.6 – 4.5	0.9 – 4.5	_	8.0	V
	(An, $\overline{OE}$ )		2.7 - 3.6		_	8.0	
			2.3 - 2.7		1	0.7	
			1.4 – 2.3		1	0.35 * V <sub>CCA</sub>	
			0.9 – 1.4		_	0.1 * V <sub>CCA</sub>	
V <sub>OH</sub>	Output HIGH Voltage	$I_{OH} = -100 \mu A; V_I = V_{IH}$	0.9 – 4.5	0.9 – 4.5	V <sub>CCB</sub> – 0.2		٧
		$I_{OH} = -0.5 \text{ mA}; V_I = V_{IH}$	0.9	0.9	0.75 * V <sub>CCB</sub>	Ms.	
		$I_{OH} = -2 \text{ mA}; V_I = V_{IH}$	1.4	1.4	1.05	S	
		$I_{OH} = -6 \text{ mA}; V_I = V_{IH}$	1.65	1.65	1.25	-	]
			2.3	2,3	2.0	-	
		$I_{OH} = -12 \text{ mA}; V_I = V_{IH}$	2.3	2.3	1.8	-	
			2.7	2.7	2.2	-	
		$I_{OH} = -18 \text{ mA}; V_I = V_{IH}$	2.3	2.3	1.7	_	
			3.0	3.0	2.4	-	
		$I_{OH} = -24 \text{ mA}; V_I = V_{IH}$	3.0	3,0	2.2	-	
V <sub>OL</sub>	Output LOW Voltage	$I_{OL} = 100 \mu\text{A};  V_{I} = V_{IL}$	0.9 – 4.5	0.9 – 4.5	7,	0.2	V
		$I_{OL} = 0.5 \text{ mA; } V_I = V_{IH}$	11(1)	(C))	_	0.3	İ
		$I_{OL} = 2 \text{ mA}; V_I = V_{IH}$	1.4	1.4	-	0.35	
		$I_{OL} = 6 \text{ mA}; V_I = V_{IL}$	1.65	1.65	-	0.3	1
		$I_{OL} = 12 \text{ mA; } V_l = V_{IL}$	2.3	2.3	-	0.4	1
		1, 00,18	2.7	2.7	_	0.4	1
	V V	$I_{OL}$ = 18 mA; $V_l$ = $V_{lL}$	2.3	2.3	_	0.6	1
	O CEISH	SV KK	3.0	3.0	_	0.45	
	CELEP	$I_{OL} = 24 \text{ mA}; V_I = V_{IL}$	3.0	3.0	_	0.6	
I <sub>I</sub>	Input Leakage Current	V <sub>I</sub> = V <sub>CCA</sub> or GND	0.9 – 4.5	0.9 – 4.5	-1.0	1.0	μÆ
I <sub>OFF</sub>	Power-Off Leakage Current	<del>OE</del> = 0 V	0 0.9 – 4.5	0.9 – 4.5 0	-1.0 -1.0	1.0 1.0	μA
I <sub>CCA</sub>	Quiescent Supply Current	$V_I = V_{CCA}$ or GND; $I_O = 0$ , $V_{CCA} = V_{CCB}$	0.9 – 4.5	0.9 – 4.5	-	2.0	μA
I <sub>CCB</sub>	Quiescent Supply Current	$V_I = V_{CCA}$ or GND; $I_O = 0$ , $V_{CCA} = V_{CCB}$	0.9 – 4.5	0.9 – 4.5	-	2.0	μÆ
CA + ICCB	Quiescent Supply Current	$V_I = V_{CCA}$ or GND; $I_O = 0$ , $V_{CCA} = V_{CCB}$	0.9 – 4.5	0.9 – 4.5	-	4.0	μA
$\Delta I_{CCA}$	Increase in I <sub>CC</sub> per Input Voltage, Other Inputs at V <sub>CCA</sub> or GND	$V_I = V_{CCA} - 0.6 V;$ $V_I = V_{CCA}$ or GND	4.5 3.6	4.5 3.6	-	10 5.0	μA
$\Delta I_{CCB}$	Increase in I <sub>CC</sub> per Input Voltage, Other Inputs at V <sub>CCA</sub> or GND	$V_I = V_{CCA} - 0.6 V;$ $V_I = V_{CCA}$ or GND	4.5 3.6	4.5 3.6	-	10 5.0	μA
I <sub>OZ</sub>	I/O Tri-State Output Leakage Current	$T_A = 25^{\circ}C$ , $\overline{OE} = 0V_{CCA}$ , $V_O = 0$ to $V_{CCB} + 0.5$ V	0.9 – 4.5	0.9 – 4.5	-	1.0	μA
		$T_A = 25$ °C, $\overline{OE} = 0V_{CCA}$ , $V_O = 0$ to 4.5 V			-	75	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

TOTAL STATIC POWER CONSUMPTION (I<sub>CCA</sub> + I<sub>CCB</sub>)

	-40°C to +85°C										
	V <sub>CCB</sub> (V)										
	4.	4.5 3.3 2.8 1.8 0.9				.9					
V <sub>CCA</sub> (V)	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	Unit
4.5		2		2		2		2		< 1.5	μΑ
3.3		2		2		2		2		< 1.5	μΑ
2.8		< 2		< 1		< 1		< 0.5		< 0.5	μА
1.8		< 1		< 1		< 0.5		< 0.5		< 0.5	μА
0.9		< 0.5		< 0.5		< 0.5		< 0.5		< 0.5	μΑ

NOTE: Connect ground before applying supply voltage V<sub>CCA</sub> or V<sub>CCB</sub>. This device is designed with the feature that the power–up sequence of V<sub>CCA</sub> and V<sub>CCB</sub> will not damage the IC.

#### **AC ELECTRICAL CHARACTERISTICS**

			-40°C to +85°C										
		,		V <sub>CCB</sub> (V)									
			4.	.5	3.	.3	2.	.8	1,	.8	1.	.5	
Symbol	Parameter	V <sub>CCA</sub> (V)	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	Unit
t <sub>PLH</sub> ,	Propagation	4.5		3.0		3.2		3.4		3.7		4.0	nS
t <sub>PHL</sub> (Note 1)	Delay,	3.6		3.3		3.5		3.7	2	4.0		4.3	
(Note 1)	A <sub>n</sub> to B <sub>n</sub>	2.8		3.5		3.7		3.9	),	4.2	17.	4.5	
		1.8		3.8		4.0		4.2	250	4.5	)`	4.8	
		1.5		4.1		4.3	10/2	4.5	1,01	4.8		5.0	
t <sub>PZH</sub> ,	Output	4.5		4.4		4.8	4.01	5.2	15/14	5.7		6.2	nS
t <sub>PZL</sub>	(Note 1)	3.3		4.7	12	5.1	7	5.5	)	6.0		6.5	
(Note 1)		2.8		4.9	·O//	5.3	` (	5.7		6.2		6.7	
		1,8		5.2	17.	5.6	$O_{k_{-}}$	6.0		6.5		7.0	
	_ (	1.5	~	5.5	14.	5.9		6.3		6.8		7.3	
t <sub>PHZ</sub> ,	Output	4.5	70	4.4	\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\	4.8		5.2		5.7		6.2	nS
t <sub>PLZ</sub> (Note 1)	Disable,	3.3	', 5	4.7	(6)	5.1		5.5		6.0		6.5	
(Note 1)	OE to B <sub>n</sub>	2.8		4.9		5.3		5.7		6.2		6.7	
		1.8		5.2		5.6		6.0		6.5		7.0	
	OF	1.5	Kr	5.5		5.9		6.3		6.8		7.3	
toshL,	Output to	4.1		0.15		0.15		0.15		0.15		0.15	nS
t <sub>OSLH</sub> (Note 1)	Output Skew, Data to Out-	3.6		0.15		0.15		0.15		0.15		0.15	
(Note I)	put	2.8		0.15		0.15		0.15		0.15		0.15	
		1.8		0.15		0.15		0.15		0.15		0.15	
		1.2		0.15		0.15		0.15		0.15		0.15	

<sup>1.</sup> Propagation delays defined per Figures 3 and 4.

#### **CAPACITANCE**

Symbol	Parameter	Test Conditions	Typ (Note 2)	Unit
C <sub>IN</sub>	Control Pin Input Capacitance	$V_{CCA} = V_{CCB} = 3.3 \text{ V}, V_I = 0 \text{ V or } V_{CCA/B}$	3.5	pF
C <sub>I/O</sub>	I/O Pin Input Capacitance	$V_{CCA} = V_{CCB} = 3.3 \text{ V}, V_I = 0 \text{ V or } V_{CCA/B}$	5.0	pF
C <sub>PD</sub>	Power Dissipation Capacitance	$V_{CCA} = V_{CCB} = 3.3 \text{ V}, V_I = 0 \text{ V or } V_{CCA}, f = 10 \text{ MHz}$	20	pF

Typical values are at T<sub>A</sub> = +25°C.
 C<sub>PD</sub> is defined as the value of the IC's equivalent capacitance from which the operating current can be calculated from: I<sub>CC(operating)</sub> ≅ C<sub>PD</sub> x V<sub>CC</sub> x f<sub>IN</sub> x N<sub>SW</sub> where I<sub>CC</sub> = I<sub>CCA</sub> + I<sub>CCB</sub> and N<sub>SW</sub> = total number of outputs switching.

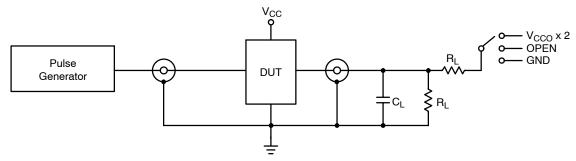


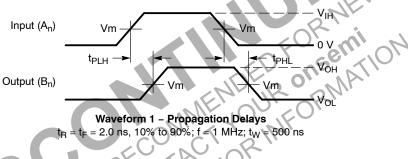
Figure 3. AC (Propagation Delay) Test Circuit

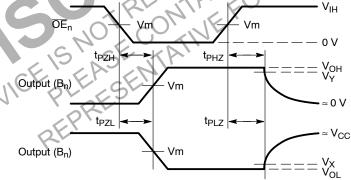
Test	Switch
t <sub>PLH</sub> , t <sub>PHL</sub>	OPEN
$t_{PLZ}$ , $t_{PZL}$	V <sub>CCO</sub> x 2
t <sub>PHZ</sub> , t <sub>PZH</sub>	GND

C<sub>L</sub> = 15 pF or equivalent (includes probe and jig capacitance)

 $R_L$  = 2  $k\Omega$  or equivalent

 $Z_{OUT}$  of pulse generator = 50  $\Omega$ 





Waveform 2 – Output Enable and Disable Times  $t_R = t_F = 2.0 \text{ ns}, 10\% \text{ to } 90\%; f = 1 \text{ MHz}; t_W = 500 \text{ ns}$ 

Figure 4. AC (Propagation Delay) Test Circuit Waveforms

	V <sub>CC</sub>							
Symbol	3.0 V – 4.5 V	2.3 V – 2.7 V	1.65 V – 1.95 V	1.4 V – 1.6 V	0.9 V – 1.3 V			
$V_{mA}$	V <sub>CCA</sub> /2							
V <sub>mB</sub>	V <sub>CCB</sub> /2							
V <sub>X</sub>	V <sub>OL</sub> x 0.1							
V <sub>Y</sub>	V <sub>OH</sub> x 0.9							

DIMENSIONING AND TOLERANCING PER ASME Y14.5M. 1994.

FROM TERMINAL TIP.

DIM

Α

A3

b D

12

T14.3M, 1994.
CONTROLLING DIMENSION: MILLIMETERS
DIMENSION 6 APPLIES TO PLATED TERMINAL
AND IS MEASURED BETWEEN 0.15 AND 0.30 MM

MOLD FLASH ALLOWED ON TERMINALS ALONG EDGE OF PACKAGE. FLASH 0.03 MAX ON BOTTOM SURFACE OF

TERMINALS.
5. DETAIL A SHOWS OPTIONAL CONSTRUCTION FOR TERMINALS.

0.55

0.03

MILLIMETERS

MIN MAX

0.00 0.05

0.127 REF

0.15 0.25

1.70 BSC

0.40 BSC

0.15 REF

0.20 0.45 0.55

0.00

0.45

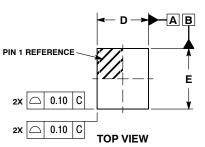


# UQFN12 1.7x2.0, 0.4P CASE 523AE

**ISSUE A** 

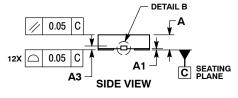
**DATE 11 JUN 2007** 



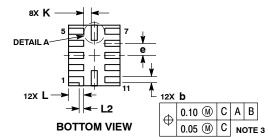












# **GENERIC MARKING DIAGRAM\***



XX = Specific Device Code

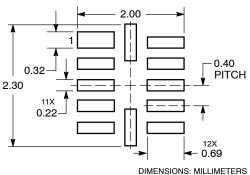
= Date Code М

NOTES:

= Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

#### **MOUNTING FOOTPRINT SOLDERMASK DEFINED**



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SOIC-14 NB CASE 751A-03 ISSUE L

**DATE 03 FEB 2016** 









- NOTES:
  1. DIMENSIONING AND TOLERANCING PER
  - ASME Y14.5M, 1994.
    CONTROLLING DIMENSION: MILLIMETERS.
- DIMENSION b DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE PROTRUSION SHALL BE 0.13 TOTAL IN EXCESS OF AT
- MAXIMUM MATERIAL CONDITION.
  DIMENSIONS D AND E DO NOT INCLUDE MOLD PROTRUSIONS.
- 5. MAXIMUM MOLD PROTRUSION 0.15 PER SIDE

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
Α	1.35	1.75	0.054	0.068
A1	0.10	0.25	0.004	0.010
АЗ	0.19	0.25	0.008	0.010
b	0.35	0.49	0.014	0.019
D	8.55	8.75	0.337	0.344
Е	3.80	4.00	0.150	0.157
е	1.27 BSC		0.050 BSC	
Н	5.80	6.20	0.228	0.244
h	0.25	0.50	0.010	0.019
L	0.40	1.25	0.016	0.049
M	0 °	7°	0 °	7°

### **GENERIC MARKING DIAGRAM\***



XXXXX = Specific Device Code Α = Assembly Location

WL = Wafer Lot Υ = Year WW = Work Week = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "■", may or may not be present. Some products may not follow the Generic Marking.

# **SOLDERING FOOTPRINT\***



DIMENSIONS: MILLIMETERS

C SEATING PLANE

#### **STYLES ON PAGE 2**

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DESCRIPTION:	SOIC-14 NB		PAGE 1 OF 2	

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<sup>\*</sup>For additional information on our Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

### SOIC-14 CASE 751A-03 ISSUE L

# DATE 03 FEB 2016

STYLE 1: PIN 1. COMMON CATHODE 2. ANODE/CATHODE 3. ANODE/CATHODE 4. NO CONNECTION 5. ANODE/CATHODE 6. NO CONNECTION 7. ANODE/CATHODE 8. ANODE/CATHODE 9. ANODE/CATHODE 10. NO CONNECTION 11. ANODE/CATHODE 12. ANODE/CATHODE 13. NO CONNECTION 14. COMMON ANODE	STYLE 2: CANCELLED	STYLE 3: PIN 1. NO CONNECTION 2. ANODE 3. ANODE 4. NO CONNECTION 5. ANODE 6. NO CONNECTION 7. ANODE 8. ANODE 9. ANODE 10. NO CONNECTION 11. ANODE 12. ANODE 13. NO CONNECTION 14. COMMON CATHODE	STYLE 4: PIN 1. NO CONNECTION 2. CATHODE 3. CATHODE 4. NO CONNECTION 5. CATHODE 6. NO CONNECTION 7. CATHODE 8. CATHODE 9. CATHODE 10. NO CONNECTION 11. CATHODE 12. CATHODE 13. NO CONNECTION 14. COMMON ANODE
STYLE 5: PIN 1. COMMON CATHODE 2. ANODE/CATHODE 3. ANODE/CATHODE 4. ANODE/CATHODE 5. ANODE/CATHODE 6. NO CONNECTION 7. COMMON ANODE 8. COMMON CATHODE 9. ANODE/CATHODE 10. ANODE/CATHODE 11. ANODE/CATHODE 12. ANODE/CATHODE 13. NO CONNECTION 14. COMMON ANODE	STYLE 6: PIN 1. CATHODE 2. CATHODE 3. CATHODE 4. CATHODE 5. CATHODE 6. CATHODE 7. CATHODE 8. ANODE 9. ANODE 10. ANODE 11. ANODE 12. ANODE 13. ANODE 14. ANODE	STYLE 7: PIN 1. ANODE/CATHODE 2. COMMON ANODE 3. COMMON CATHODE 4. ANODE/CATHODE 5. ANODE/CATHODE 6. ANODE/CATHODE 7. ANODE/CATHODE 8. ANODE/CATHODE 9. ANODE/CATHODE 10. ANODE/CATHODE 11. COMMON CATHODE 12. COMMON ANODE 13. ANODE/CATHODE 14. ANODE/CATHODE	STYLE 8: PIN 1. COMMON CATHODE 2. ANODE/CATHODE 3. ANODE/CATHODE 4. NO CONNECTION 5. ANODE/CATHODE 6. ANODE/CATHODE 7. COMMON ANODE 8. COMMON ANODE 9. ANODE/CATHODE 10. ANODE/CATHODE 11. NO CONNECTION 12. ANODE/CATHODE 13. ANODE/CATHODE 14. COMMON CATHODE

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**DATE 17 FEB 2016** 

- NOTES:

  1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

  2. CONTROLLING DIMENSION: MILLIMETER.

  3. DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
  DIMENSION B DOES NOT INCLUDE
- INTERLEAD FLASH OR PROTRUSION.
  INTERLEAD FLASH OR PROTRUSION SHALL
- INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION. TERMINAL NUMBERS ARE SHOWN FOR DEEEDERING ONLY
- REFERENCE ONLY.
  DIMENSION A AND B ARE TO BE
- DETERMINED AT DATUM PLANE -W-.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
Α	4.90	5.10	0.193	0.200
В	4.30	4.50	0.169	0.177
С		1.20		0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65 BSC		0.026 BSC	
Н	0.50	0.60	0.020	0.024
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
L	6.40 BSC		0.252 BSC	
М	o°	8 °	0 °	8 °

#### **GENERIC MARKING DIAGRAM\***



= Assembly Location

= Wafer Lot Υ = Year

= Work Week W

= Pb-Free Package

(Note: Microdot may be in either location)

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "■", may or may not be present. Some products may not follow the Generic Marking.

| DETAIL E  0.15 (0.006) T U S  A  O.10 (0.004)   4. [<br>4. [<br>1<br>5. [<br>6. ]<br>7. [<br>7. [ |
|---|---|
| SOLDERING FOOTPRINT  7.06  1  | A<br>L<br>Y<br>V                                  |
| 0.65 PITCH  | (Note:  |

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